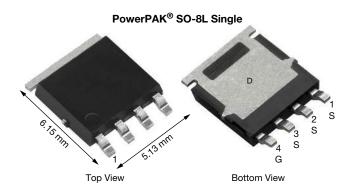


Vishay Siliconix

Automotive P-Channel 80 V (D-S) 175 °C MOSFET



| PRODUCT SUMMARY | | | | |
|---|--------|--|--|--|
| V _{DS} (V) | -80 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$ | 0.033 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$ | 0.044 | | | |
| I _D (A) | -32 | | | |
| Configuration | Single | | | |

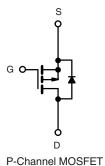
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



| ORDERING INFORMATION | |
|---------------------------------|--|
| Package | PowerPAK SO-8L |
| Lead (Pb)-free and halogen-free | SQJ479EP (for detailed order number please see www.vishay.com/doc?79771) |

| ABSOLUTE MAXIMUM RATINGS | (T _C = 25 °C, unles | s otherwise noted |) | | |
|--|--------------------------------|-----------------------------------|-------------|----|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Drain-source coltage | | V_{DS} | -80 | V | |
| Gate-source coltage | | V _{GS} | ± 20 | V | |
| Continuous drain current | T _C = 25 °C | | -32 | | |
| Continuous drain current | T _C = 125 °C | I _D | -18 | | |
| Continuous source current (diode conduction) | I _S | -60 | Α | | |
| Pulsed drain current b | | I _{DM} | -100 | | |
| Single pulse avalanche current | | I _{AS} | -40 | | |
| Single pulse avalanche energy L = 0.1 mH | | E _{AS} | 80 | mJ | |
| Maximum power dissipation ^b | T _C = 25 °C | - P _D | 68 | W | |
| Maximum power dissipation - | T _C = 125 °C | | 22 | | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +175 | °C | |
| Soldering recommendations (peak temperature | e) ^{d, e} | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|-------------|------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction to ambient | PCB mount c | R_{thJA} | 68 | °C/W |
| Junction to case (drain) | | R_{thJC} | 2.2 | C/VV |

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|--------------------------|---|--|------|--------|--------|------|
| Static | | 1 | | | | ı | ı |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} | = 0, I _D = -250 μA | -80 | - | - | V |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | V _{GS} , I _D = -250 μA | -1.5 | -2.0 | -2.5 | V |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA |
| | | V _{GS} = 0 V | V _{DS} = -80 V | - | - | -1 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = -80 V, T _J = 125 °C | - | - | -50 | μΑ |
| | | V _{GS} = 0 V | V _{DS} = -80 V, T _J = 175 °C | - | - | -150 | 1 |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = -10 V | $V_{DS} \ge -5 \text{ V}$ | -30 | - | - | Α |
| | | V _{GS} = -10 V | I _D = -10 A | - | 0.0275 | 0.0330 | |
| Dunin Course On Chata Basistana 3 | | V _{GS} = -10 V | I _D = -10 A, T _J = 125 °C | - | - | 0.0544 | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = -10 V | I _D = -10 A, T _J = 175 °C | _ | - | 0.0670 | Ω |
| | | V _{GS} = -4.5 V | I _D = -5 A | _ | 0.0360 | 0.0440 | |
| Forward Transconductance b | 9 _{fs} | V _{DS} = | -15 V, I _D = -10 A | _ | 25 | - | S |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 3290 | 4500 | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ | V _{DS} = -25 V, f = 1 MHz | - | 320 | 450 | pF |
| Reverse Transfer Capacitance | C _{rss} | 1 | | - | 215 | 300 | 1 1 |
| Total Gate Charge ^c | Qg | | | - | 90 | 150 | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = -10 V | $V_{DS} = -40 \text{ V}, I_{D} = -10 \text{ A}$ | _ | 11 | - | nC |
| Gate-Drain Charge ^c | Q _{gd} | 1 | | _ | 24 | - | |
| Gate Resistance | R_g | | f = 1 MHz | 0.50 | 1.16 | 1.80 | Ω |
| Turn-On Delay Time ^c | t _{d(on)} | | | - | 15 | 25 | |
| Rise Time ^c | t _r | V _{DD} = | = -40 V, R _I = 10 Ω | - | 5 | 10 | |
| Turn-Off Delay Time ^c | t _{d(off)} | | $V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$ | - | 50 | 80 | ns |
| Fall Time ^c | t _f | 1 | | - | 6 | 10 | 1 |
| Source-Drain Diode Ratings and Chara | acteristics ^b | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | -100 | Α |
| Forward Voltage | V_{SD} | I _F = -10 A, V _{GS} = 0 | | - | -0.85 | -1.2 | V |

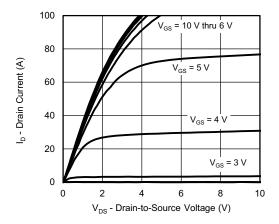
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

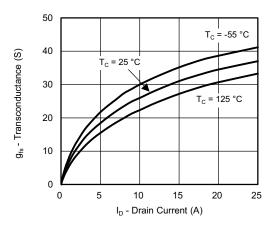
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



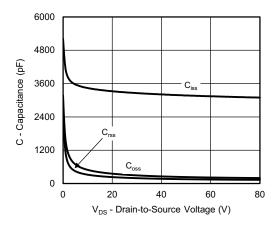
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



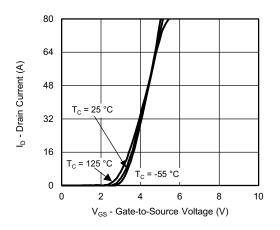
Output Characteristics



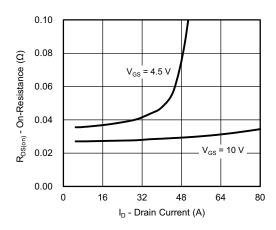
Transconductance



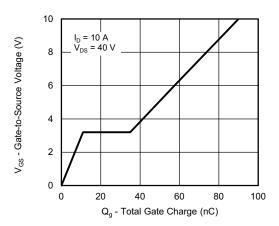
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current

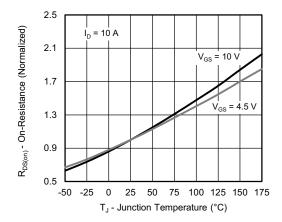


Gate Charge

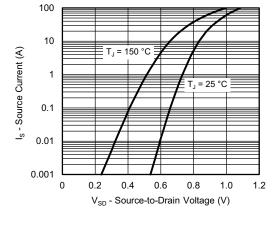
For technical questions, contact: automostechsur



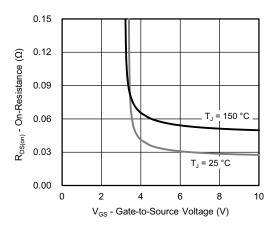
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



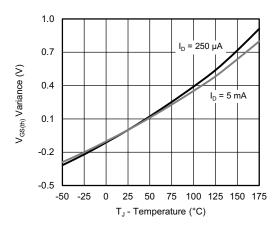
On-Resistance vs. Junction Temperature



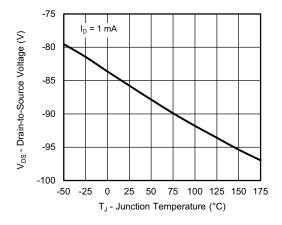
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



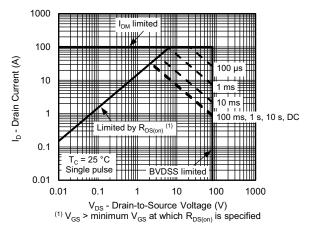
Threshold Voltage



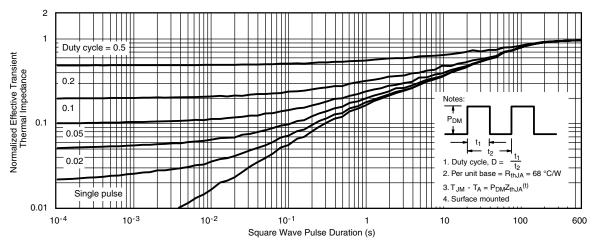
Drain-Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



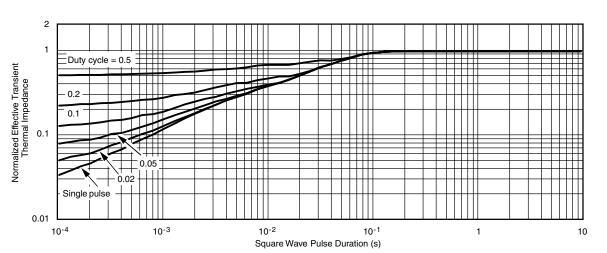
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

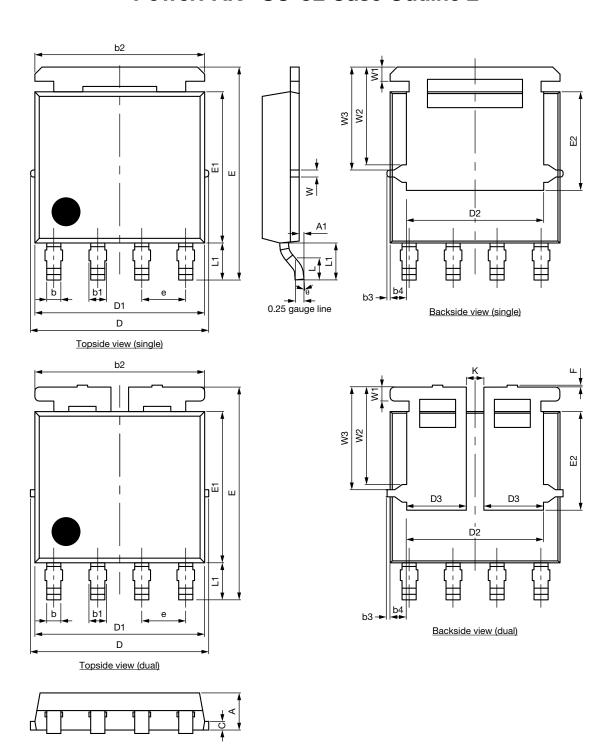
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg275129.



PowerPAK® SO-8L Case Outline 2



www.vishay.com Vishay Siliconix

| DIM. | MILLIMETERS | | | INCHES | | | |
|------|-------------|----------|-------|-----------|-------|-------|--|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| А | 1.00 | 1.07 | 1.14 | 0.039 | 0.042 | 0.045 | |
| A1 | 0.00 | - | 0.127 | 0.00 | - | 0.005 | |
| b | 0.33 | 0.41 | 0.48 | 0.013 | 0.016 | 0.019 | |
| b1 | 0.44 | 0.51 | 0.58 | 0.017 | 0.020 | 0.023 | |
| b2 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 | |
| b3 | | 0.094 | _ | | 0.004 | • | |
| b4 | | 0.47 | | | 0.019 | | |
| С | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 | |
| D | 5.00 | 5.13 | 5.25 | 0.197 | 0.202 | 0.207 | |
| D1 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 | |
| D2 | 3.86 | 3.96 | 4.06 | 0.152 | 0.156 | 0.160 | |
| D3 | 1.63 | 1.73 | 1.83 | 0.064 | 0.068 | 0.072 | |
| е | | 1.27 BSC | • | 0.050 BSC | | | |
| E | 6.05 | 6.15 | 6.25 | 0.238 | 0.242 | 0.246 | |
| E1 | 4.27 | 4.37 | 4.47 | 0.168 | 0.172 | 0.176 | |
| E2 | 2.75 | 2.85 | 2.95 | 0.108 | 0.112 | 0.116 | |
| F | - | - | 0.15 | - | - | 0.006 | |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 | |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 | |
| K | | 0.51 | • | 0.020 | | | |
| W | 0.23 | | 0.009 | | | | |
| W1 | 0.41 | | 0.016 | | | | |
| W2 | | 2.82 | | 0.111 | | | |
| W3 | | 2.96 | | | 0.117 | | |
| θ | 0° | - | 10° | 0° | - | 10° | |

ECN: C21-1498-Rev. C, 01-Nov-2021

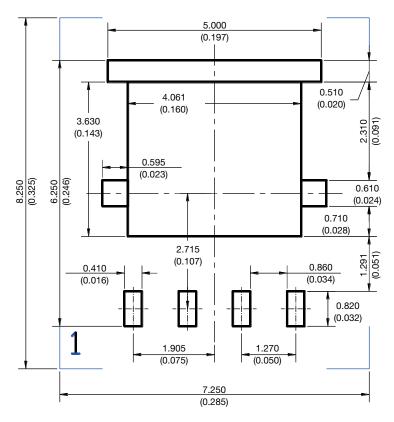
DWG: 6044

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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